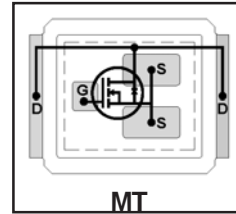


# IRF6618/IRF6618TR1

HEXFET® Power MOSFET

- Application Specific MOSFETs
- Ideal for CPU Core DC-DC Converters
- Low Conduction Losses
- Low Switching Losses
- Low Profile (<0.7 mm)
- Dual Sided Cooling Compatible
- Compatible with existing Surface Mount Techniques

$V_{DS}$	$R_{DS(on)}$ max	$Q_g$
30V	2.2mΩ @ $V_{GS} = 10V$	43 nC
	3.4mΩ @ $V_{GS} = 4.5V$	



Applicable DirectFET Package/Layout Pad (see p.8,9 for details)

SQ	SX	ST		MQ	MX	<b>MT</b>				
----	----	----	--	----	----	-----------	--	--	--	--

## Description

The IRF6618 combines the latest HEXFET® Power MOSFET Silicon technology with the advanced DirectFET™ packaging to achieve the lowest on-state resistance in a package that has the footprint of an SO-8 and only 0.7 mm profile. The DirectFET package is compatible with existing layout geometries used in power applications, PCB assembly equipment and vapor phase, infra-red or convection soldering techniques, when application note AN-1035 is followed regarding the manufacturing methods and processes. The DirectFET package allows dual sided cooling to maximize thermal transfer in power systems, IMPROVING previous best thermal resistance by 80%.

The IRF6618 balances both low resistance and low charge along with ultra low package inductance to reduce both conduction and switching losses. The reduced total losses make this product ideal for high efficiency DC-DC converters that power the latest generation of processors operating at higher frequencies. The IRF6618 has been optimized for parameters that are critical in synchronous buck converters including  $R_{ds(on)}$ , gate charge and  $C_{dv/dt}$ -induced turn on immunity. The IRF6618 offers particularly low  $R_{ds(on)}$  and high  $C_{dv/dt}$  immunity for synchronous FET applications.

## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain-to-Source Voltage	30	V
$V_{GS}$	Gate-to-Source Voltage	±20	
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	150	A
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	30	
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	24	
$I_{DM}$	Pulsed Drain Current ①	240	
$P_D @ T_A = 25^\circ C$	Power Dissipation ②	2.8	W
$P_D @ T_A = 70^\circ C$	Power Dissipation ②	1.8	
$P_D @ T_C = 25^\circ C$	Power Dissipation	89	
	Linear Derating Factor	0.022	W/°C
$T_J$	Operating Junction and	-40 to + 150	°C
$T_{STG}$	Storage Temperature Range		

## Avalanche Characteristics

	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy ②	—	210	mJ
$I_{AR}$	Avalanche Current ①	—	24	A

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ④③	—	45	°C/W
$R_{\theta JA}$	Junction-to-Ambient ⑤	12.5	—	
$R_{\theta JA}$	Junction-to-Ambient ⑥	20	—	
$R_{\theta JC}$	Junction-to-Case ⑦	—	1.4	
$R_{\theta J-PCB}$	Junction-to-PCB Mounted	1.0	—	

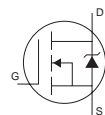
Notes ① through ⑧ are on page 9  
www.irf.com

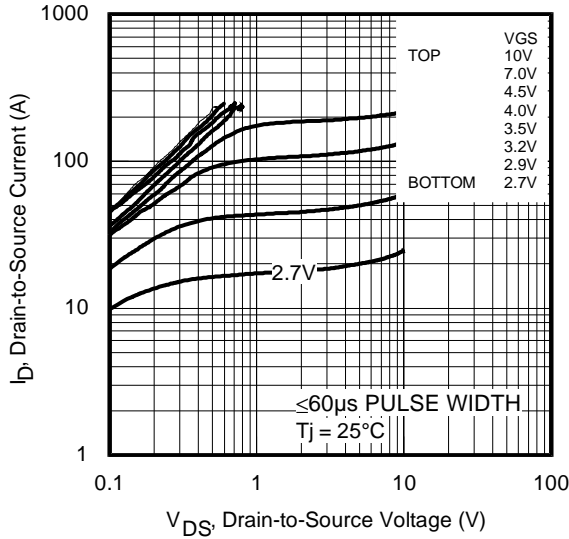
## Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$BV_{DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	23	—	mV/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	1.7	2.2	m $\Omega$	$V_{GS} = 10V, I_D = 30A$ ③
		—	—	3.4		$V_{GS} = 4.5V, I_D = 24A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.35	1.64	2.35	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-5.7	—	mV/ $^\circ\text{C}$	
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	5.0	$\mu A$	$V_{DS} = 30V, V_{GS} = 0V$
		—	—	1.0		$V_{DS} = 24V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 24V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
$g_{fs}$	Forward Transconductance	100	—	—	S	$V_{DS} = 15V, I_D = 24A$
$Q_g$	Total Gate Charge	—	43	65	nC	$V_{DS} = 15V$ $V_{GS} = 4.5V$ $I_D = 24A$ See Fig. 16
$Q_{gs1}$	Pre-Vth Gate-to-Source Charge	—	12	—		
$Q_{gs2}$	Post-Vth Gate-to-Source Charge	—	4.0	—		
$Q_{gd}$	Gate-to-Drain Charge	—	15	23		
$Q_{godr}$	Gate Charge Overdrive	—	12	—		
$Q_{sw}$	Switch Charge ( $Q_{gs2} + Q_{gd}$ )	—	19	—		
$Q_{oss}$	Output Charge	—	28	—	nC	$V_{DS} = 15V, V_{GS} = 0V$
$R_G$	Gate Resistance	—	1.0	2.2	$\Omega$	
$t_{d(on)}$	Turn-On Delay Time	—	21	—	ns	$V_{DD} = 15V, V_{GS} = 4.5V$ ③ $I_D = 24A$ Clamped Inductive Load
$t_r$	Rise Time	—	71	—		
$t_{d(off)}$	Turn-Off Delay Time	—	27	—		
$t_f$	Fall Time	—	8.1	—		
$C_{iss}$	Input Capacitance	—	5640	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	1260	—		$V_{DS} = 15V$
$C_{rss}$	Reverse Transfer Capacitance	—	570	—		$f = 1.0\text{MHz}$

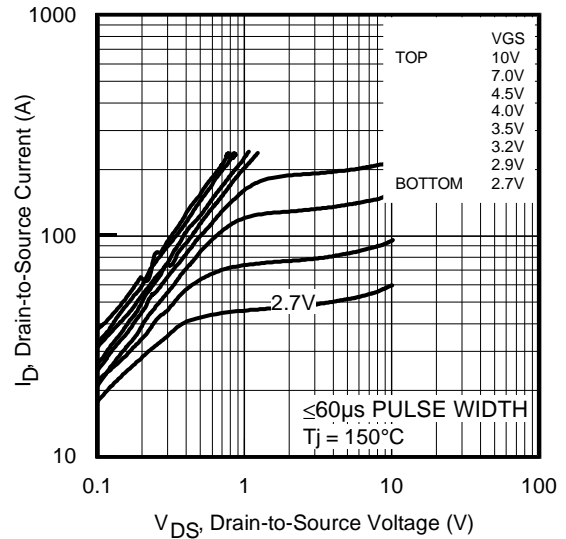
## Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	30	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	240		
$V_{SD}$	Diode Forward Voltage	—	0.78	1.2	V	$T_J = 25^\circ\text{C}, I_S = 24A, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	43	65	ns	$T_J = 25^\circ\text{C}, I_F = 24A$
$Q_{rr}$	Reverse Recovery Charge	—	46	69	nC	$di/dt = 100A/\mu s$ ③

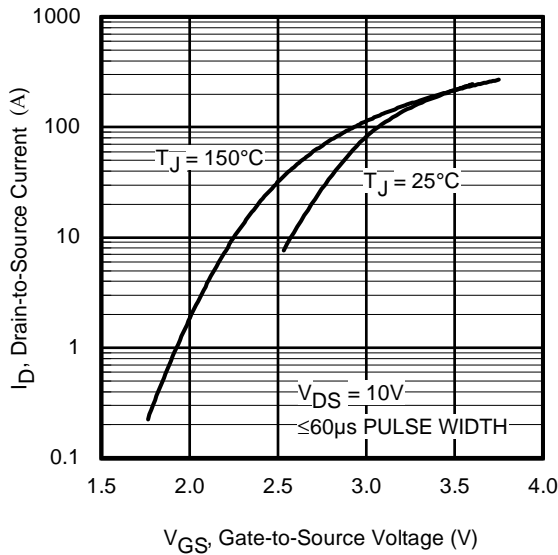




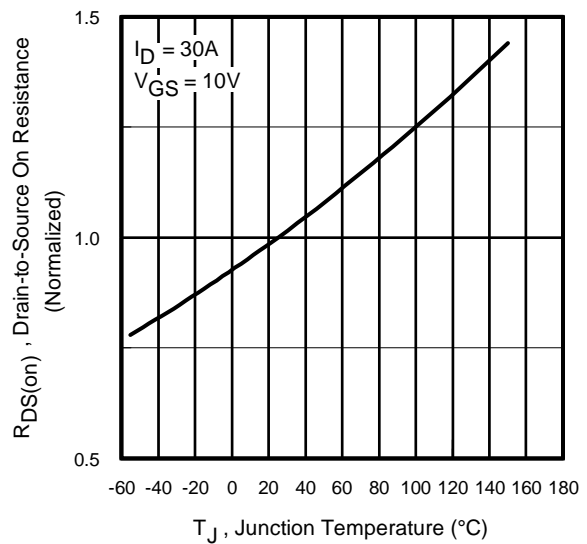
**Fig 1.** Typical Output Characteristics



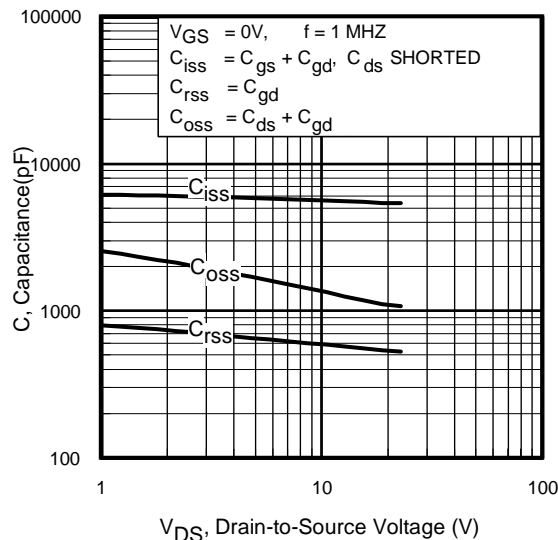
**Fig 2.** Typical Output Characteristics



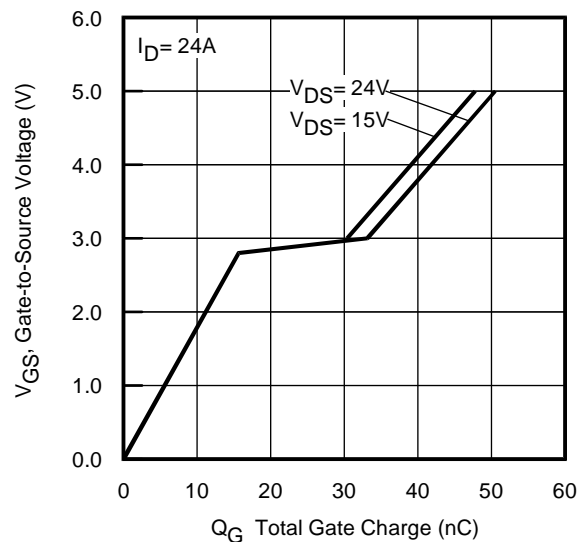
**Fig 3.** Typical Transfer Characteristics



**Fig 4.** Normalized On-Resistance vs. Temperature



**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage

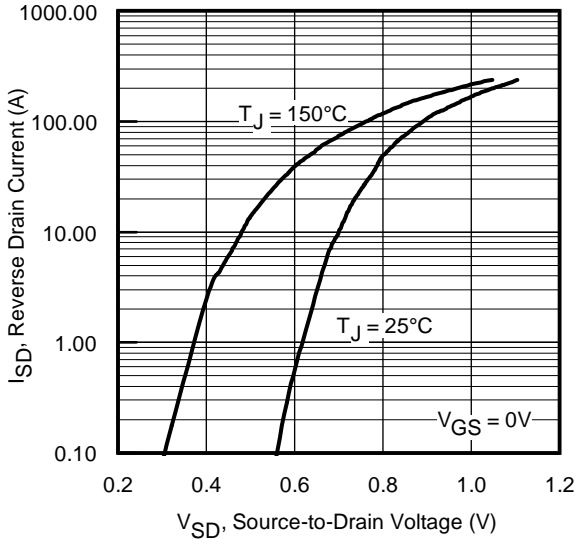


Fig 7. Typical Source-Drain Diode Forward Voltage

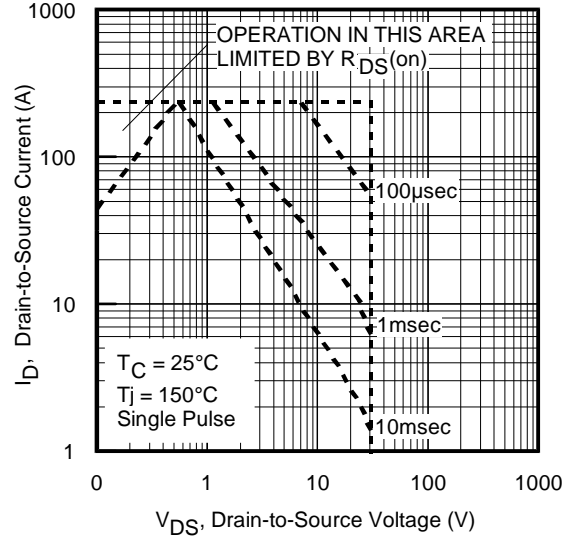


Fig 8. Maximum Safe Operating Area

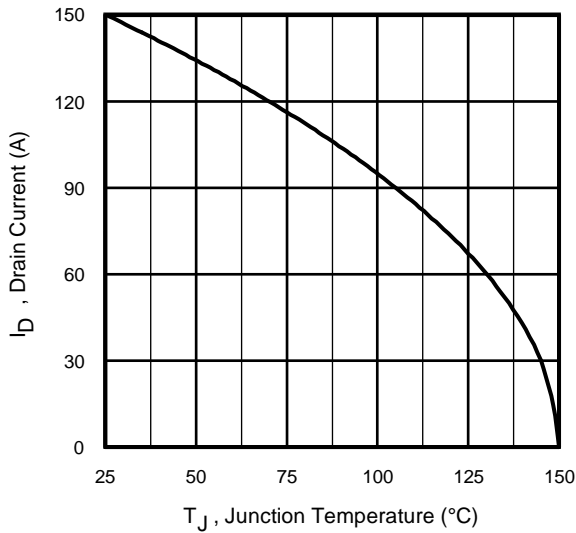


Fig 9. Maximum Drain Current vs. Case Temperature

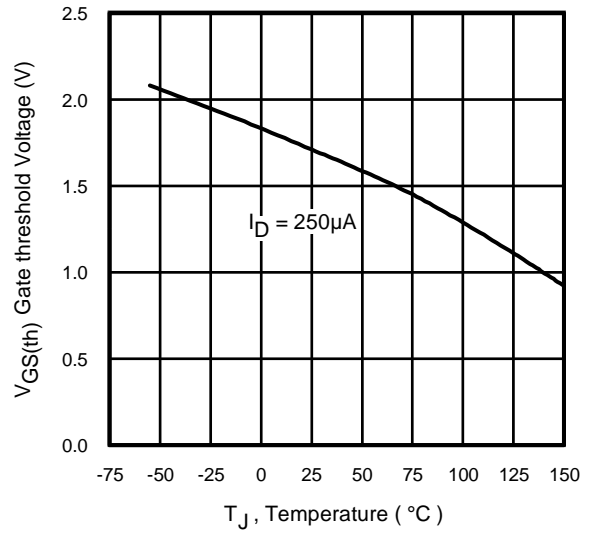


Fig 10. Threshold Voltage vs. Temperature

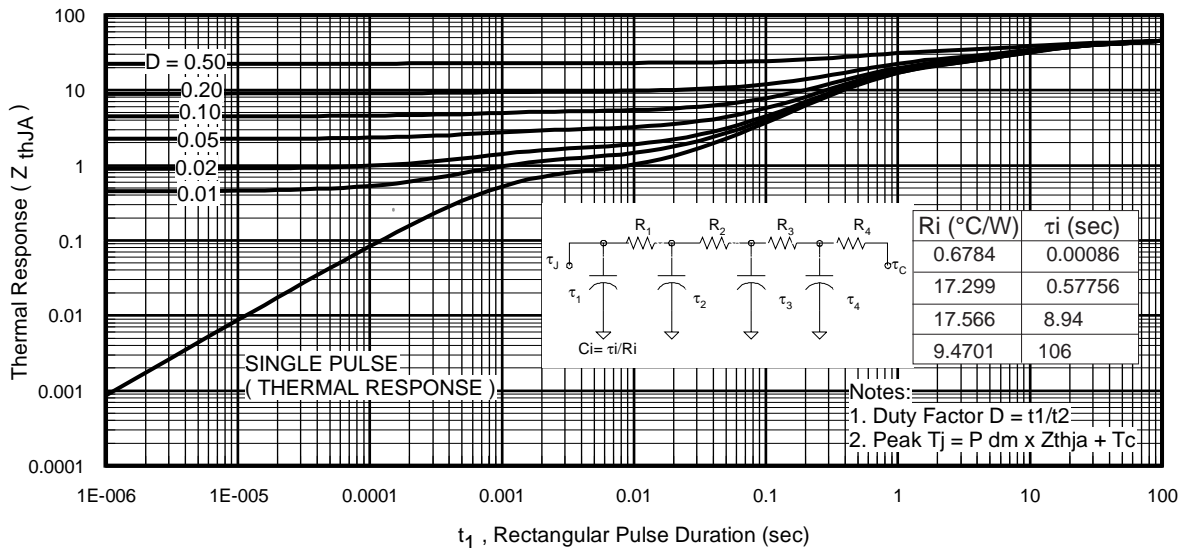
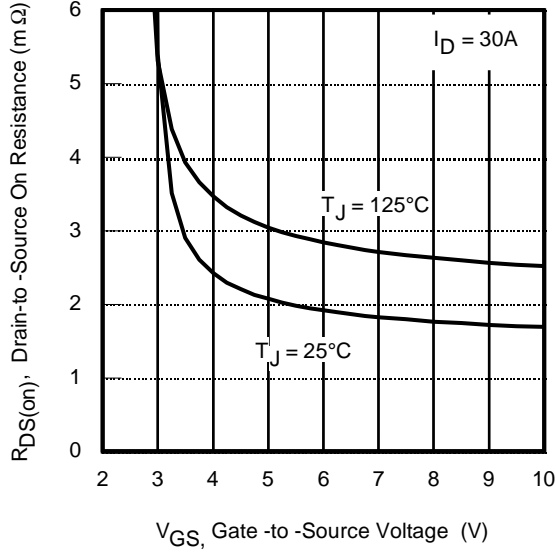
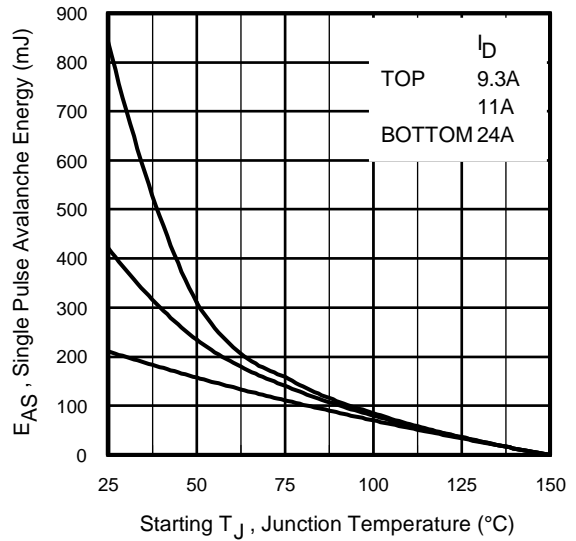


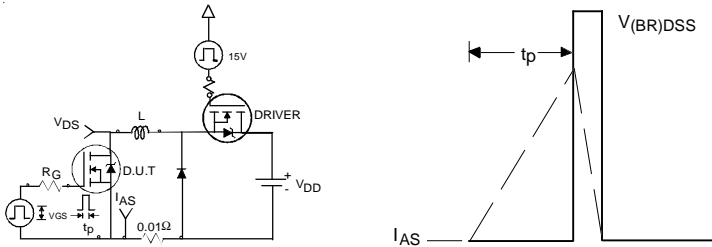
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



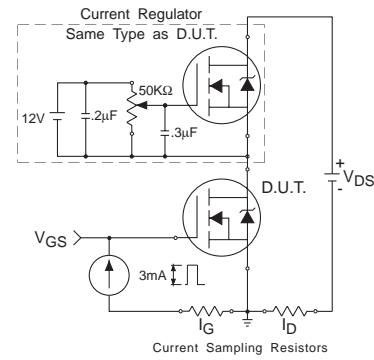
**Fig 12. On-Resistance vs. Gate Voltage**



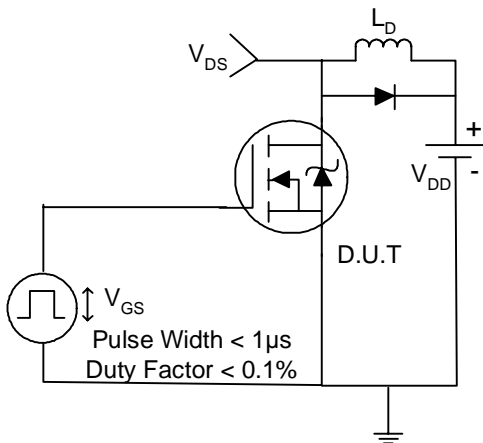
**Fig 13. Maximum Avalanche Energy vs. Drain Current**



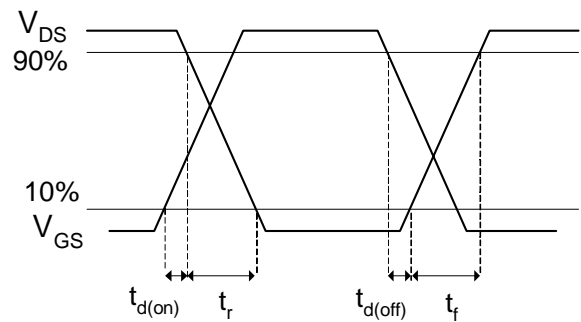
**Fig 14. Unclamped Inductive Test Circuit and Waveform**



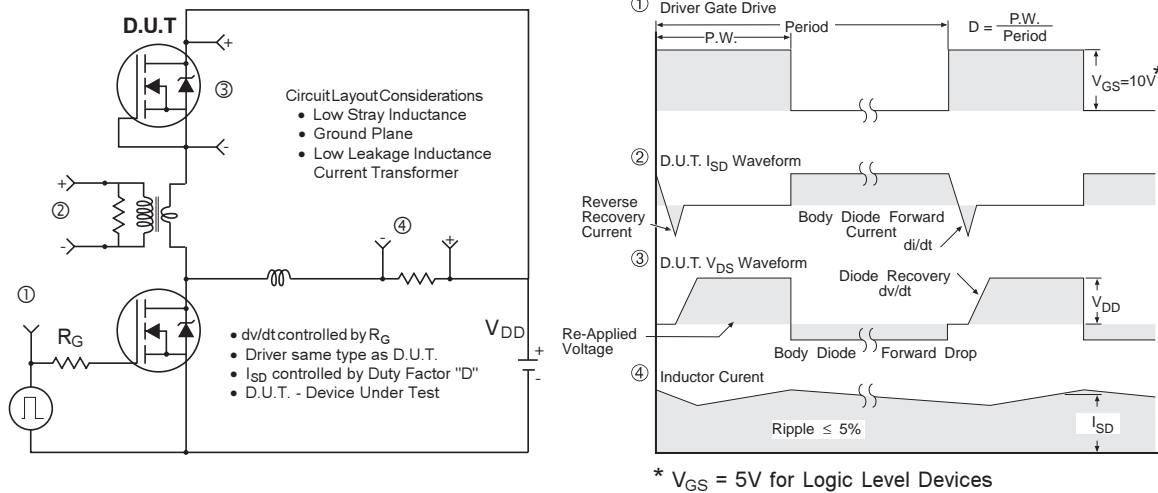
**Fig 15. Gate Charge Test Circuit**



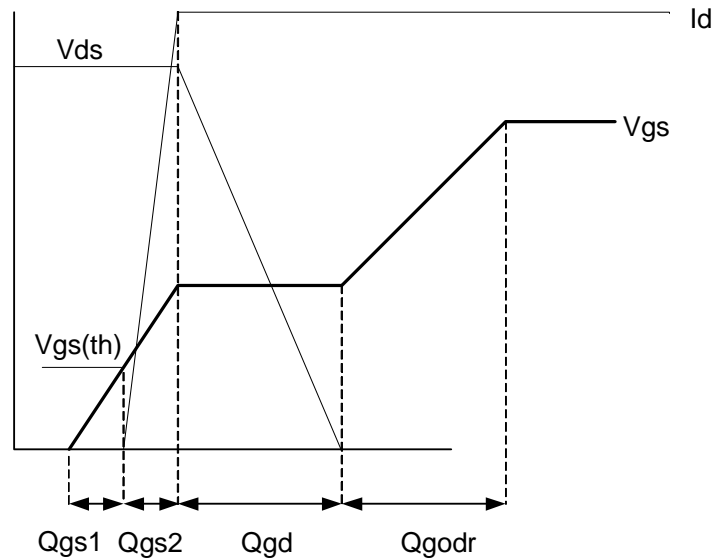
**Fig 16. Switching Time Test Circuit**



**Fig 17. Switching Time Waveforms**



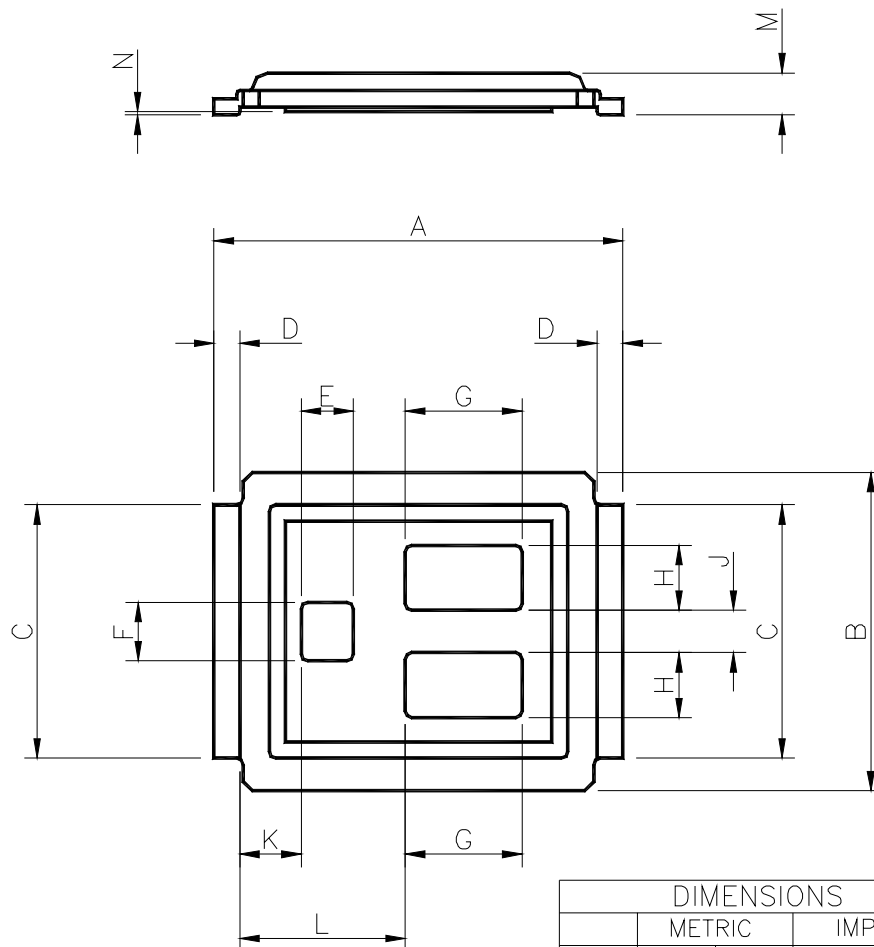
**Fig 15. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs**



**Fig 16. Gate Charge Waveform**

## DirectFET™ Outline Dimension, MT Outline (Medium Size Can, T-Designation).

Please see DirectFET application note AN-1035 for all details regarding the assembly of DirectFET. This includes all recommendations for stencil and substrate designs.



Note: Controlling dimensions are in mm

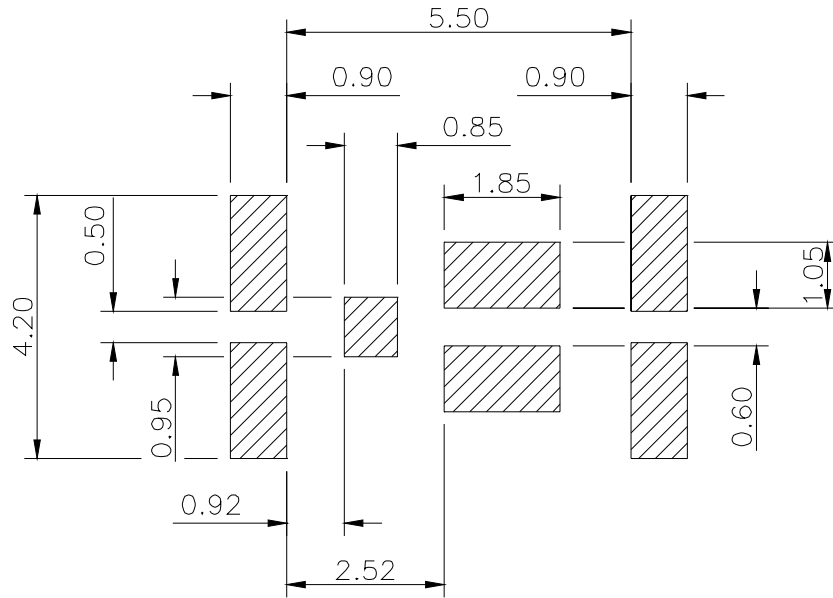
DIMENSIONS				
CODE	METRIC		IMPERIAL	
	MIN	MAX	MIN	MAX
A	6.25	6.35	0.246	0.250
B	4.80	5.05	0.189	0.201
C	3.85	3.95	0.152	0.156
D	0.35	0.45	0.014	0.018
E	0.78	0.82	0.031	0.032
F	0.88	0.92	0.035	0.036
G	1.78	1.82	0.070	0.072
H	0.98	1.02	0.039	0.040
J	0.63	0.67	0.025	0.026
K	0.88	1.01	0.035	0.039
L	2.46	2.63	0.097	0.104
M	0.59	0.70	0.023	0.028
N	0.03	0.08	0.001	0.003

# IRF6618/IRF6618TR1

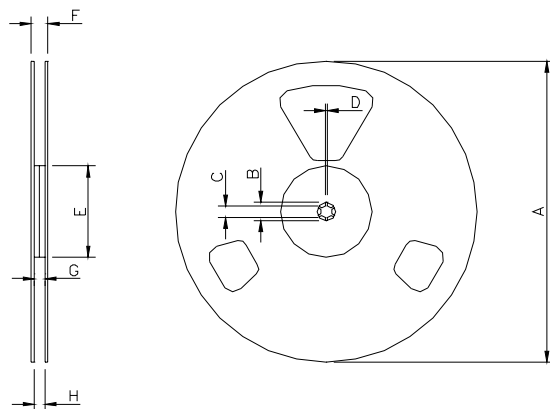
## DirectFET™ Board Footprint, MT Outline (Medium Size Can, T-Designation).

Please see DirectFET application note AN-1035 for all details regarding the assembly of DirectFET.

This includes all recommendations for stencil and substrate designs.

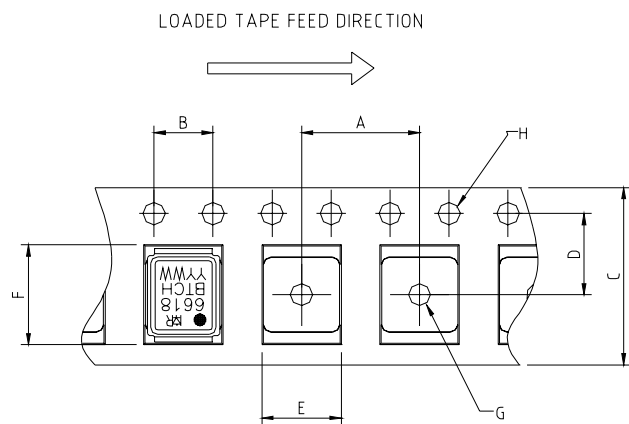


## DirectFET™ Tape & Reel Dimension (Showing component orientation).



NOTE: Controlling dimensions in mm  
Std reel quantity is 4800 parts. (ordered as IRF6618). For 1000 parts on 7" reel,  
order IRF6618TR1

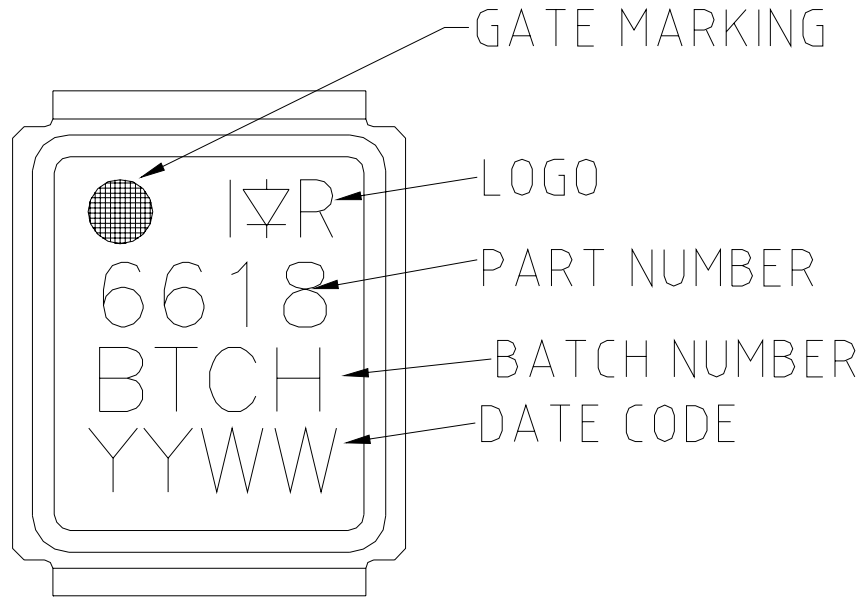
CODE	REEL DIMENSIONS							
	STANDARD OPTION (QTY 4800)				TR1 OPTION (QTY 1000)			
	METRIC		IMPERIAL		METRIC		IMPERIAL	
A	330.0	N.C	12.992	N.C	177.77	N.C	6.9	N.C
B	20.2	N.C	0.795	N.C	19.06	N.C	0.75	N.C
C	12.8	13.2	0.504	0.520	13.5	12.8	0.53	0.50
D	1.5	N.C	0.059	N.C	1.5	N.C	0.059	N.C
E	100.0	N.C	3.937	N.C	58.72	N.C	2.31	N.C
F	N.C	18.4	N.C	0.724	N.C	13.50	N.C	0.53
G	12.4	14.4	0.488	0.567	11.9	12.01	0.47	N.C
H	11.9	15.4	0.469	0.606	11.9	12.01	0.47	N.C



NOTE: CONTROLLING DIMENSIONS IN MM

CODE	DIMENSIONS			
	METRIC		IMPERIAL	
A	7.90	8.10	0.311	0.319
B	3.90	4.10	0.154	0.161
C	11.90	12.30	0.469	0.484
D	5.45	5.55	0.215	0.219
E	5.10	5.30	0.201	0.209
F	6.50	6.70	0.256	0.264
G	1.50	N.C	0.059	N.C
H	1.50	1.60	0.059	0.063

## DirectFET™ Part Marking



### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.75\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 24\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ Surface mounted on 1 in. square Cu board.
- ⑤ Used double sided cooling , mounting pad.
- ⑥ Mounted on minimum footprint full size board with metalized back and with small clip heatsink.
- ⑦  $T_C$  measured with thermal couple mounted to top (Drain) of part.
- ⑧  $R_\theta$  is measured at  $T_J$  of approximately  $90^\circ\text{C}$ .

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Consumer market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information.03/04



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

[LittleDiode.com](http://LittleDiode.com)

Looking forward to providing you with the best possible service.